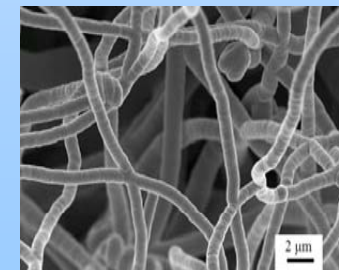
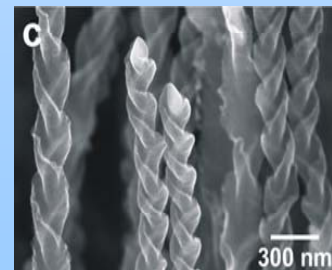
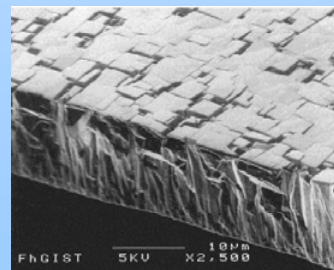
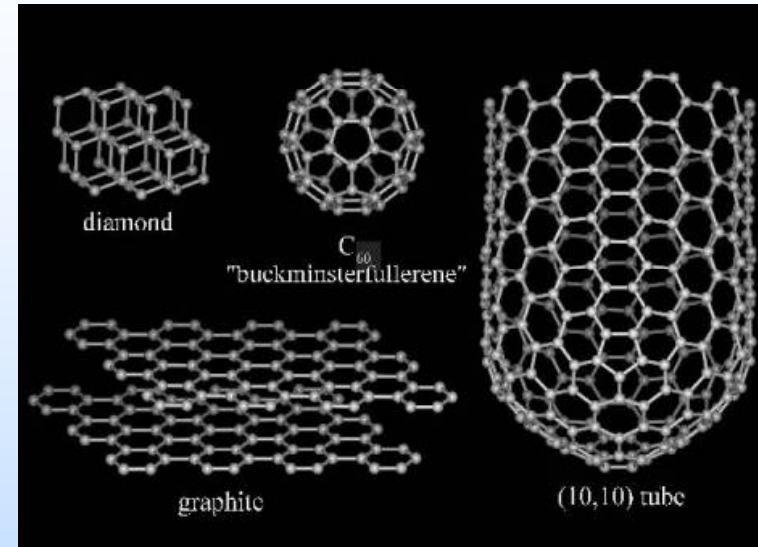


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Content

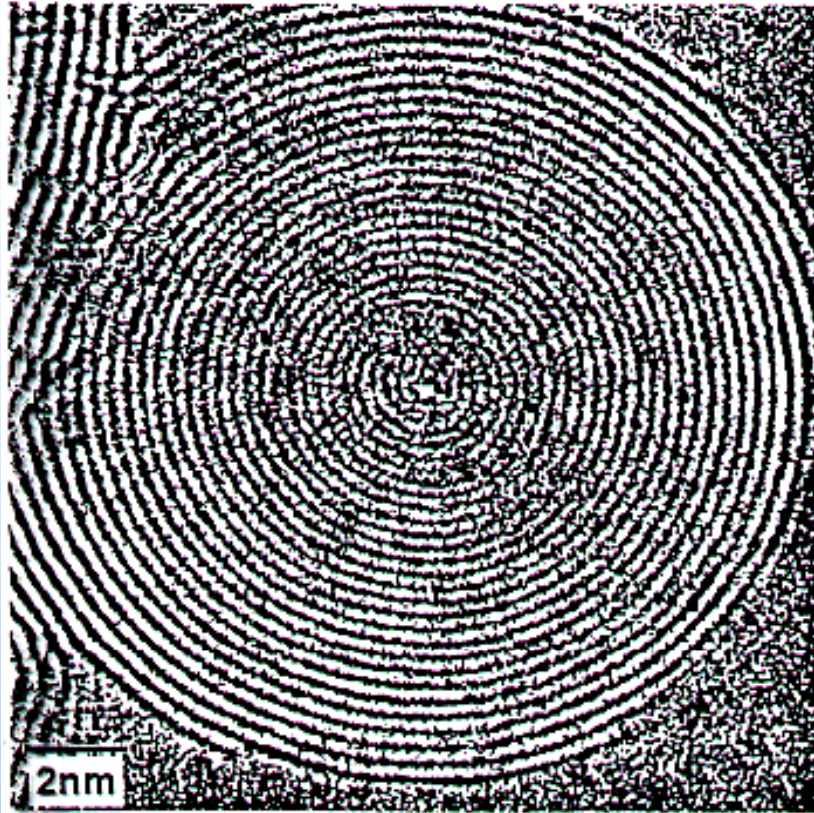
- CVD-diamond films
- Graded nano-crystalline composite coatings
- a-C:H and Me-C:H films



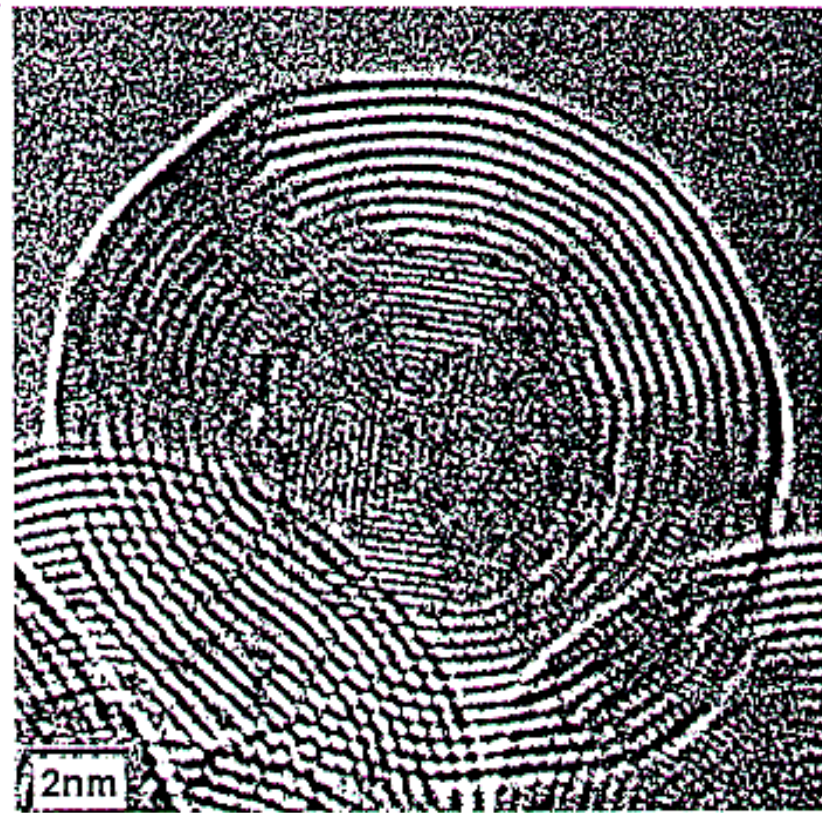
Intrinsic properties of diamond and applications

Hardness (Hv)	100 GPa	Cutting tools and machine part coating
Chemical resistance	Against all chemicals	Electrodes for the chemical Industry
Thermo-conductivity λ	20 W/cmK	Isolating heat sinks for Laser diode
Breakthrough field strength E_s	10^7 V/cm	
Transparency	UV-, VIS u. IR	Optic window for UV- bis -IR range
Refraction index n	2,42	
Absorption edge	200 nm	
Band gap E_g	5,45 eV	High temperature semiconductor and sensor materials (bis 600 °C, for Si 120 °C)
Carrier mobility μ , <i>Electron</i>	2200 cm ² /Vs	
<i>Hole</i>	1600 cm ² /Vs	

Low pressure diamond growth

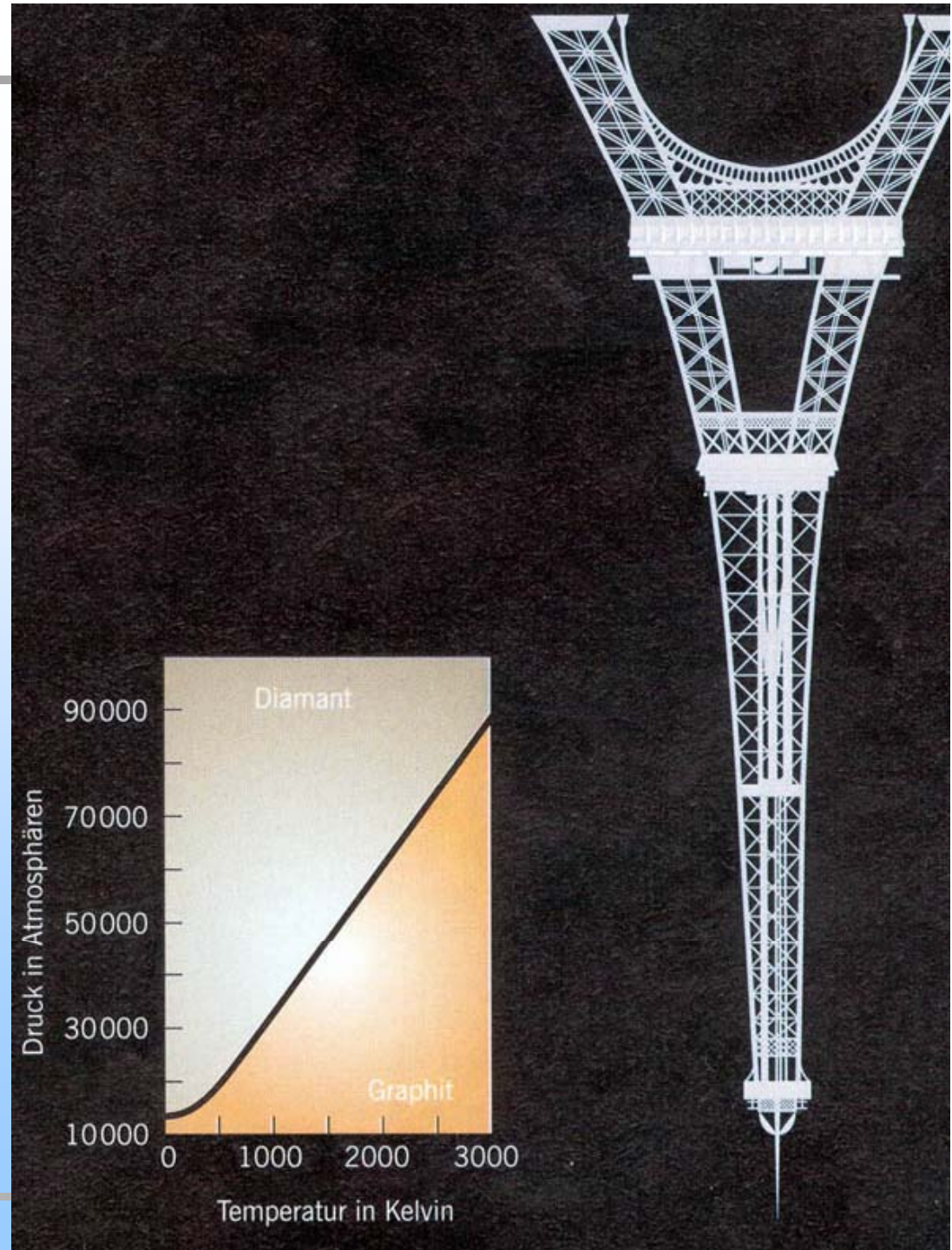


Spherical, Graphite



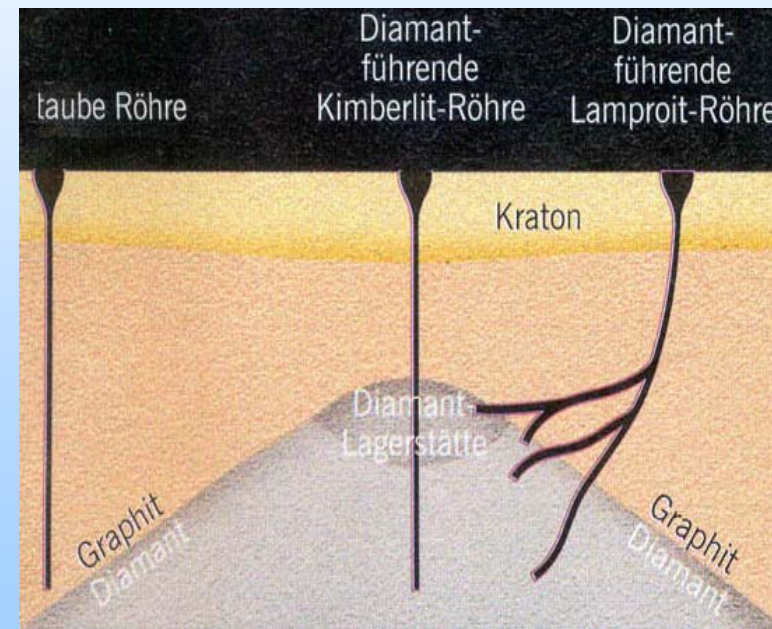
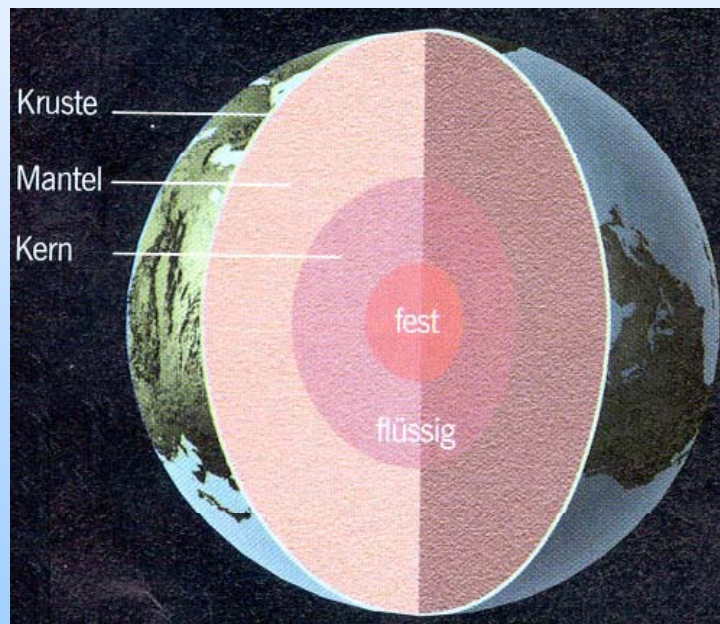
Graphite with diamond core.
Created by electron irradiation
at 1000 K

Kohlenstoff- Phasendiagramm

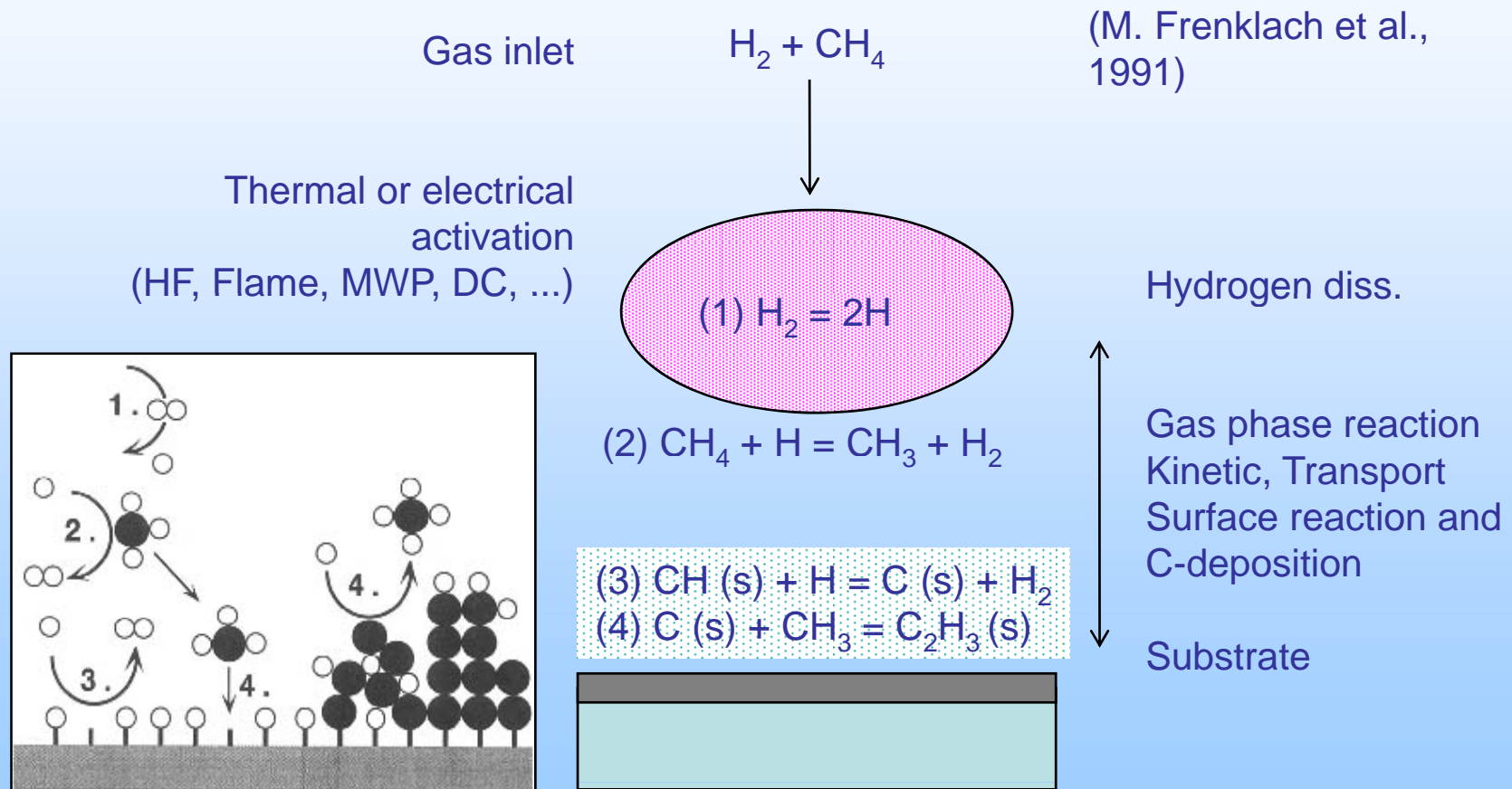


Die Herkunft von Diamant

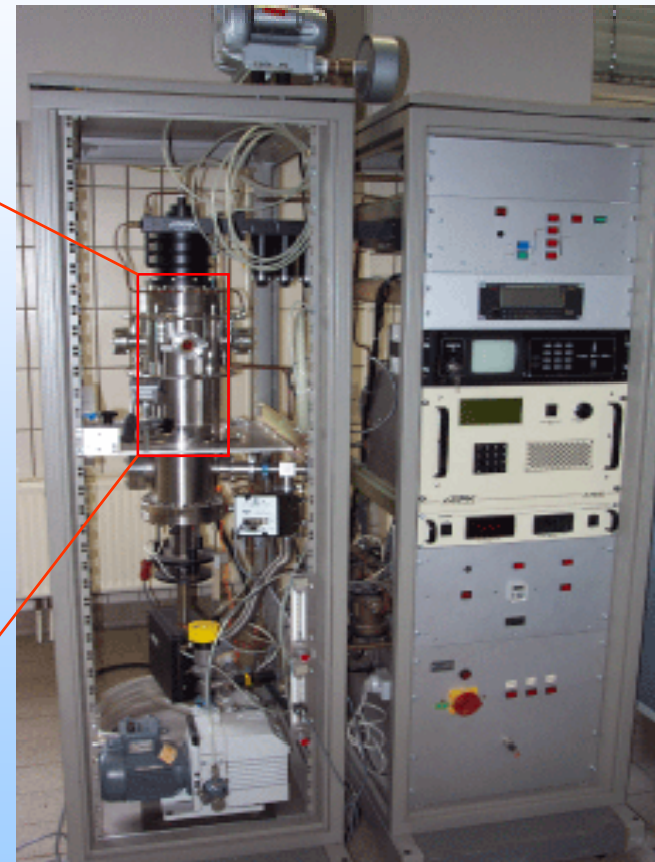
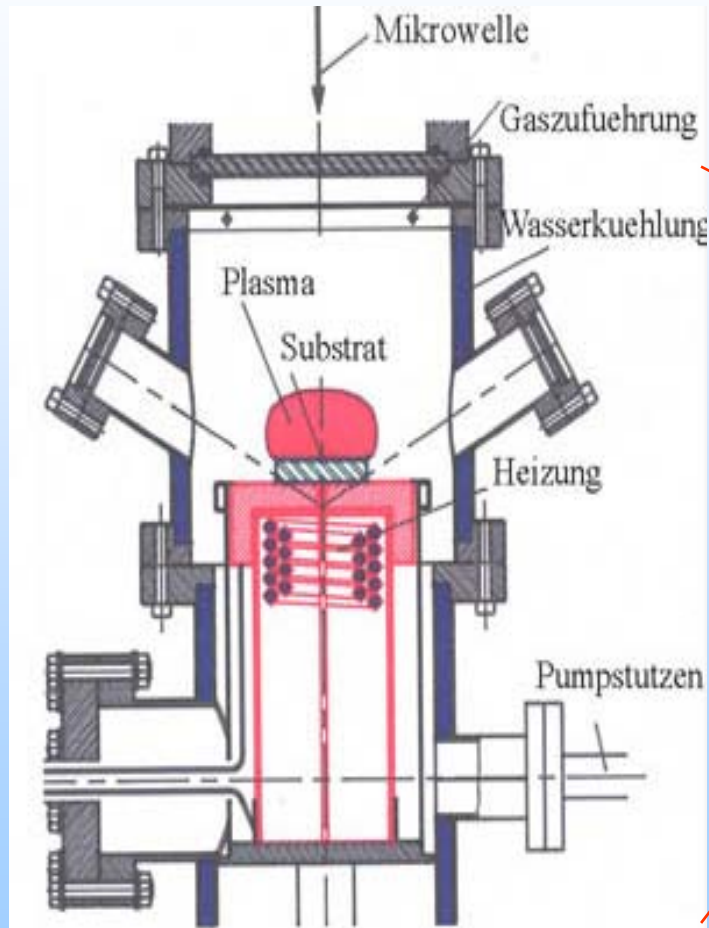
(Spektrum der Wissenschaft Jan. 1999)



CVD-Diamond deposition

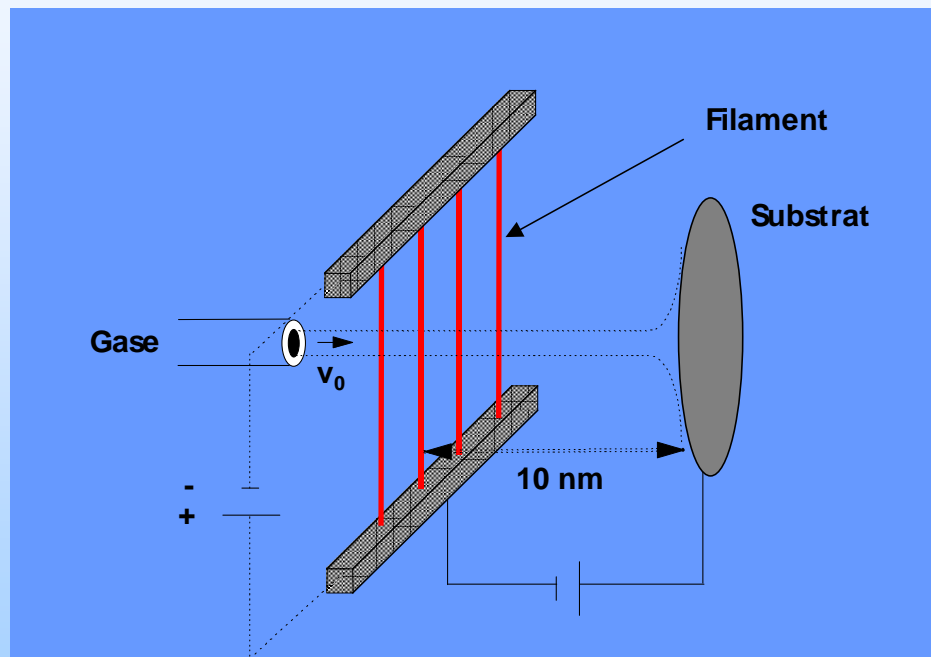


Microwave-Plasma-CVD



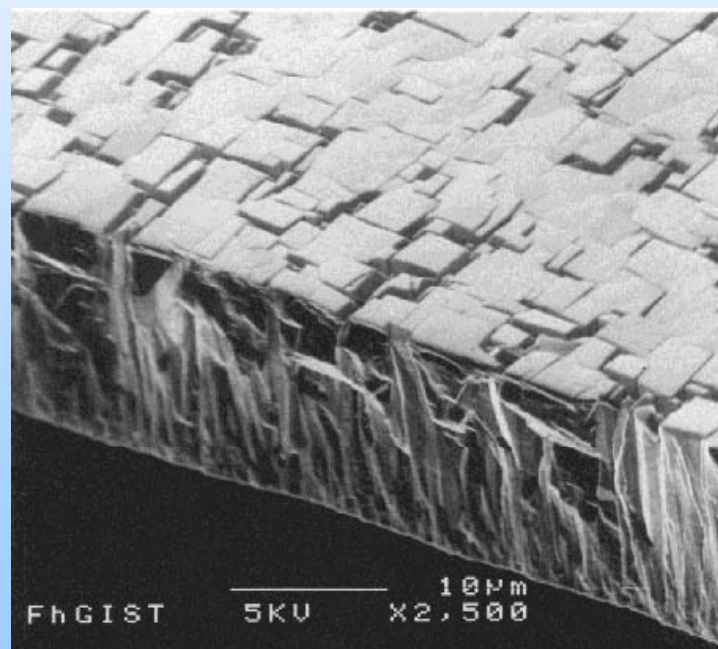
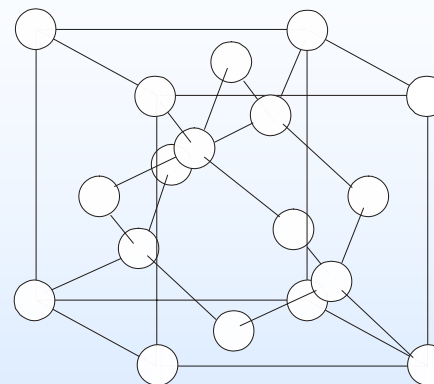
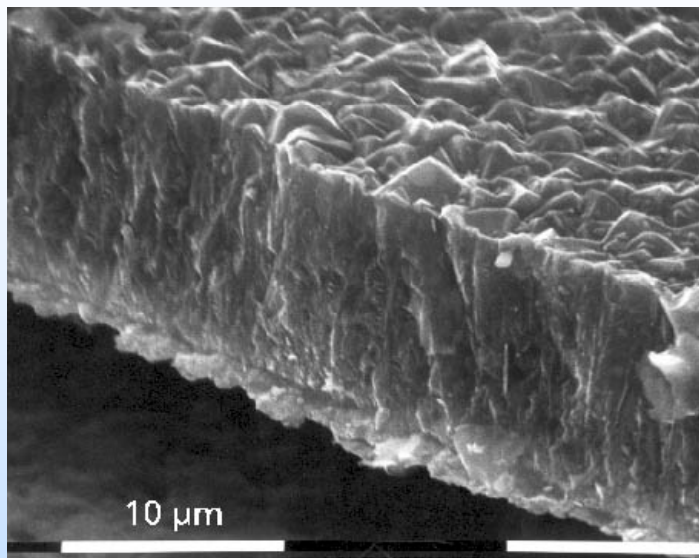
$T_s = 500 - 700 \text{ C}$, $\text{CH}_4/\text{H}_2 = 1:98-99.5$, $p = 10 - 40 \text{ mbar}$, $P = 500 - 1000 \text{ W}$

Hot-Filament-CVD



$T_F = 2200 \text{ }^\circ\text{C}$, $T_S = 500 - 900 \text{ }^\circ\text{C}$, $\text{CH}_4/\text{H}_2 = 0,5 - 2\%$, Druck = 10 - 40 mbar

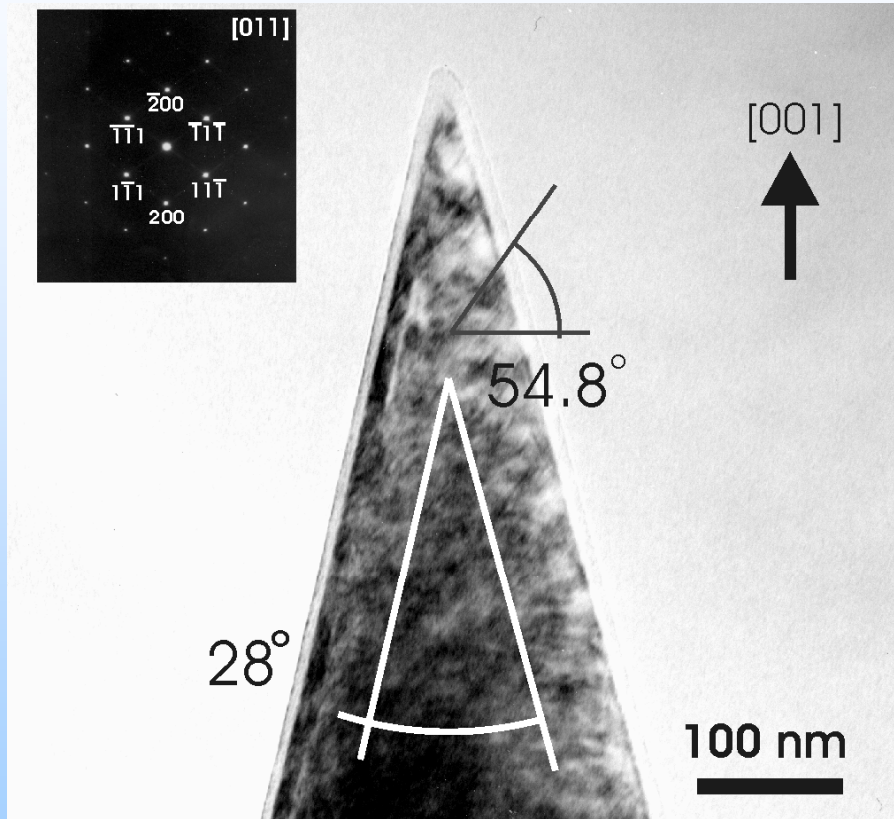
Structure of diamond films



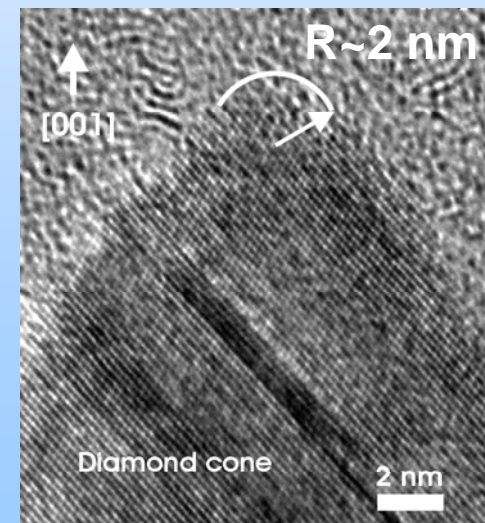
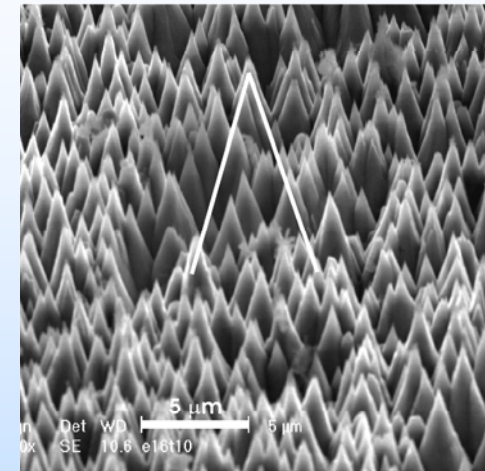
Material	Lattice constant	Surface Energy
Diamond	3,5667 Å	ca. 6,0 J/m ²
c-BN	3,612 Å	4,8 J/m ²
Si	5,4388 Å	1,5 J/m ²

Appl. Phys. Lett. 62, 3438 (1993)

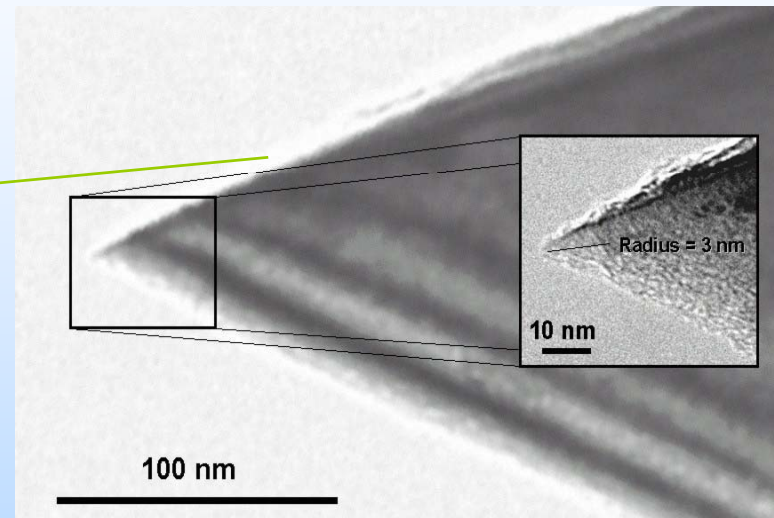
AFM (Atomic Force Microscopy)-Tips



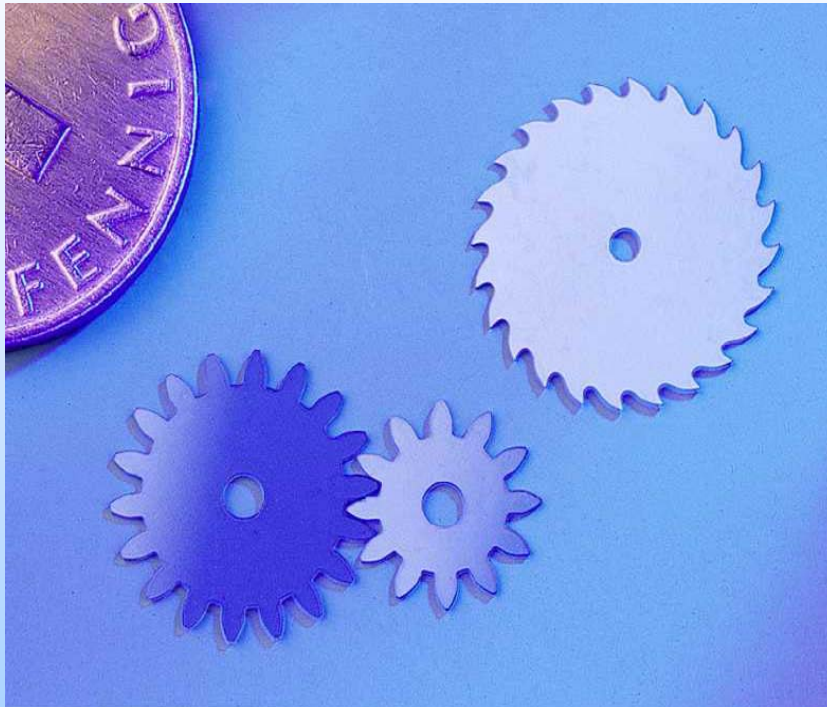
Single crystalline; Tip angle $\sim 28^\circ$;
[001]-oriented



Diamond scalpels with atomic tip cutting edges



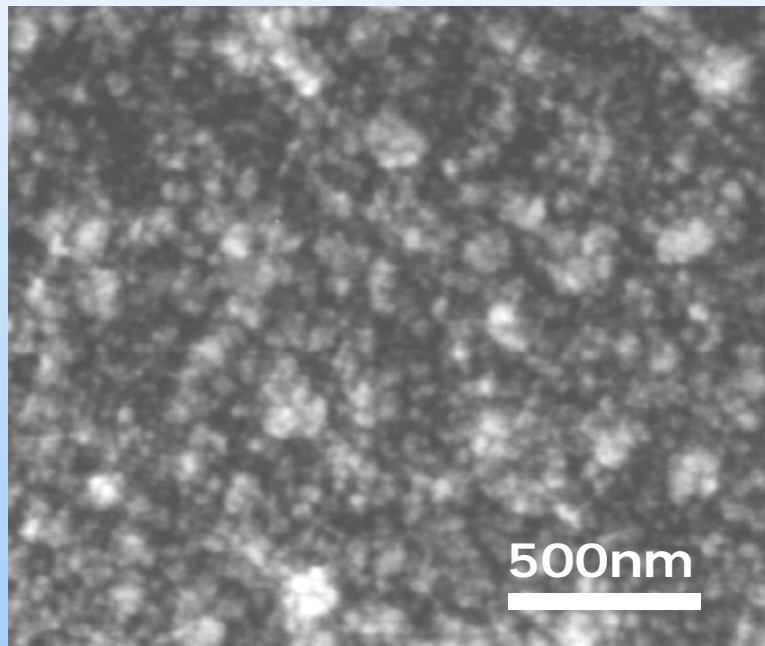
Machine parts for micromechanics



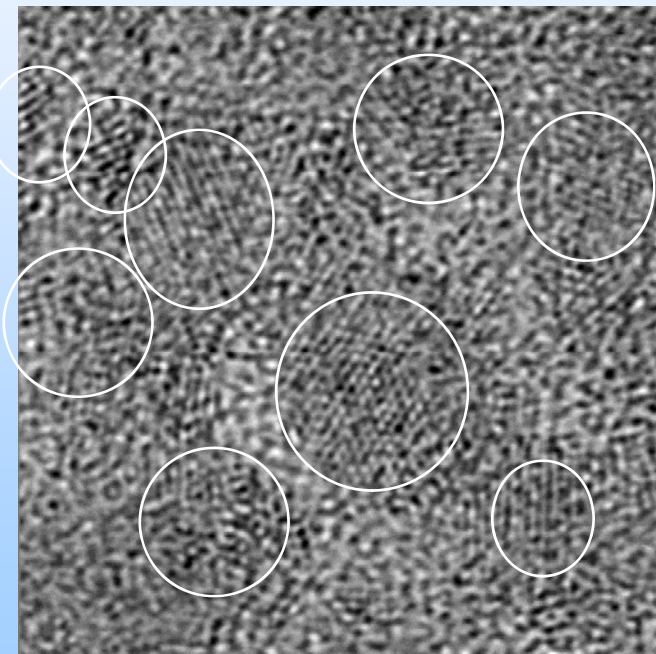
Computer controlled laser cutting (Nd:YAG)

Synthesis of nanodiamond

- Ion bombardment induced nucleation

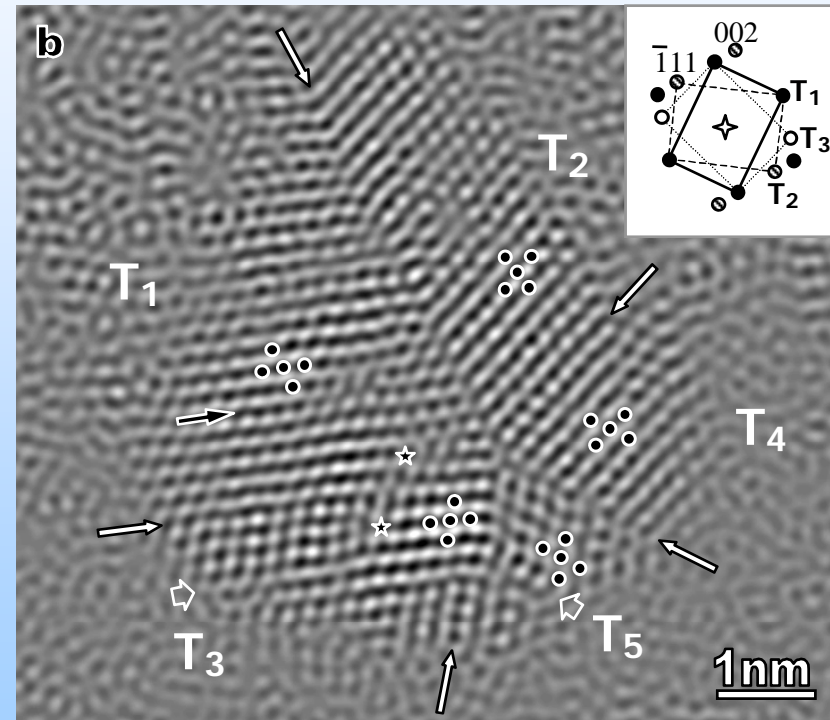
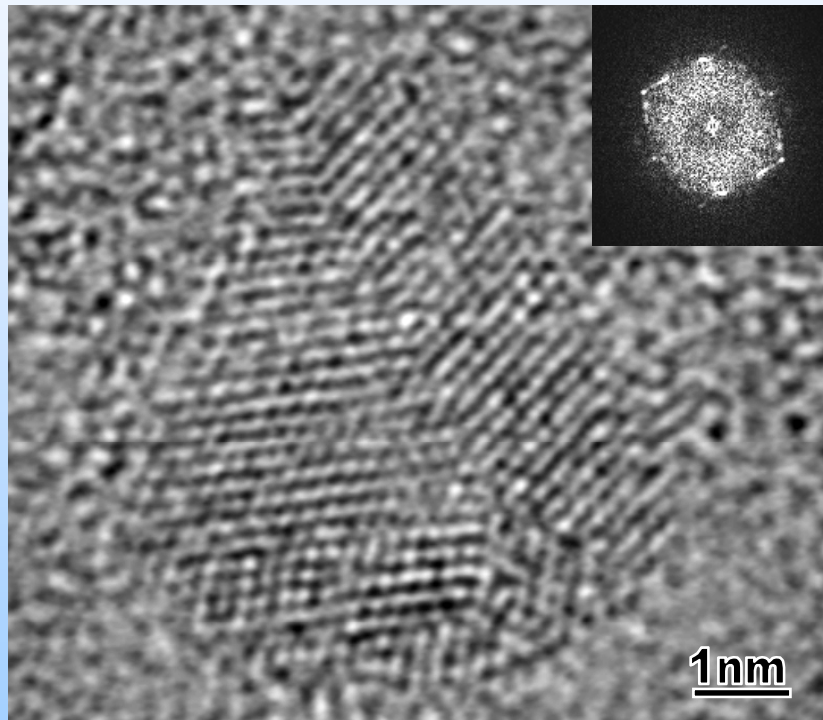


Surface roughness = 2 nm

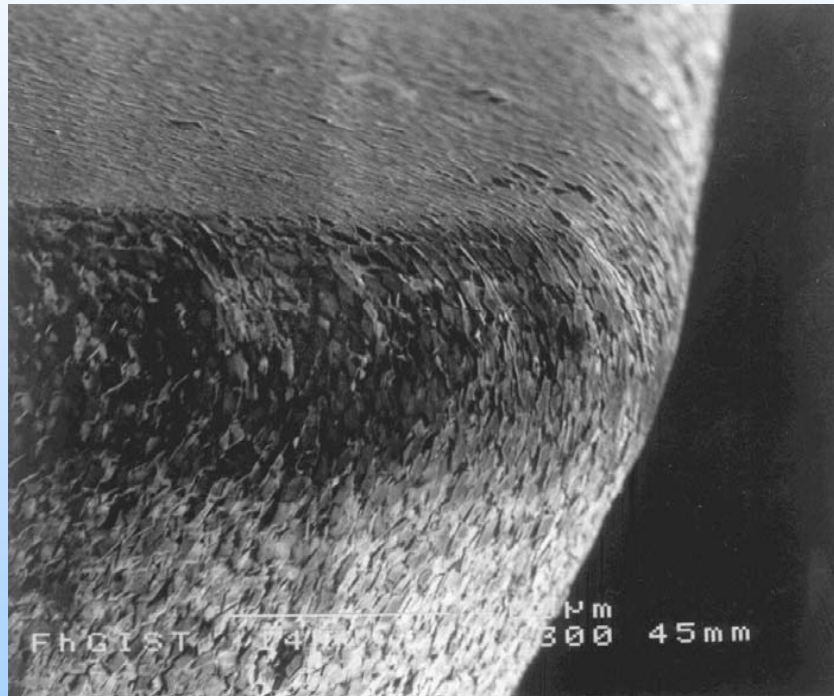


Grain size = 10 nm

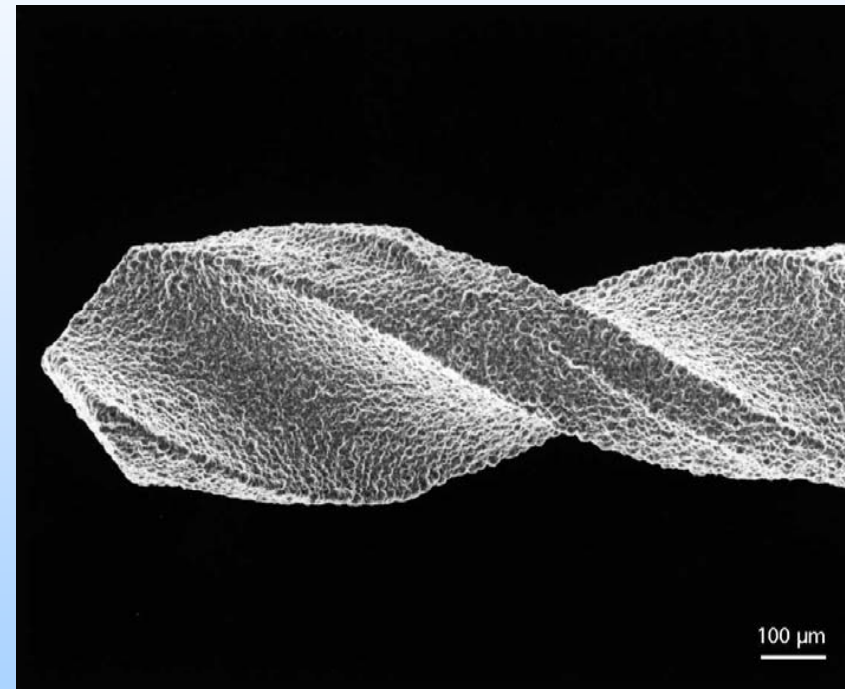
HRTEM-images of nanodiamond



Coating of cutting tools

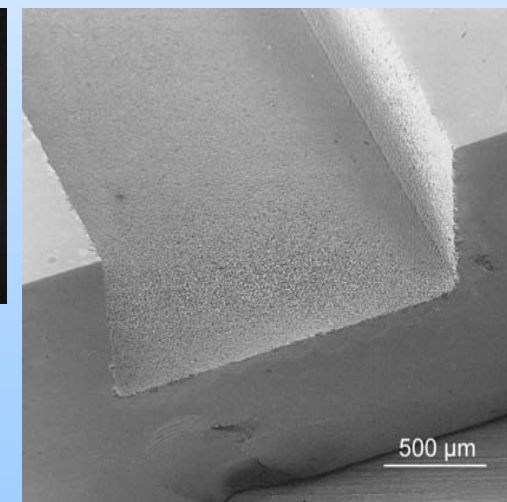
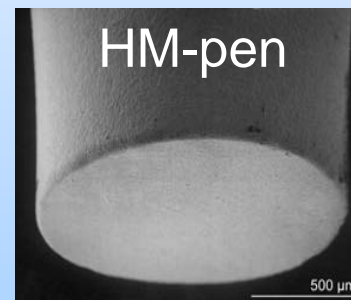
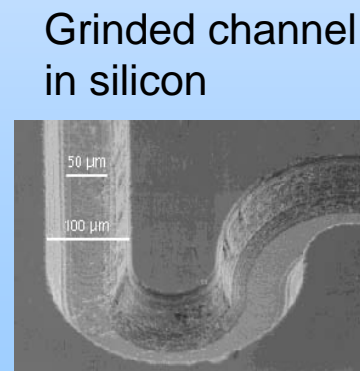
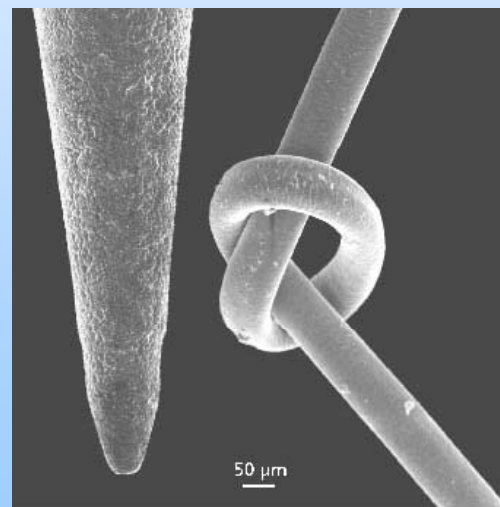
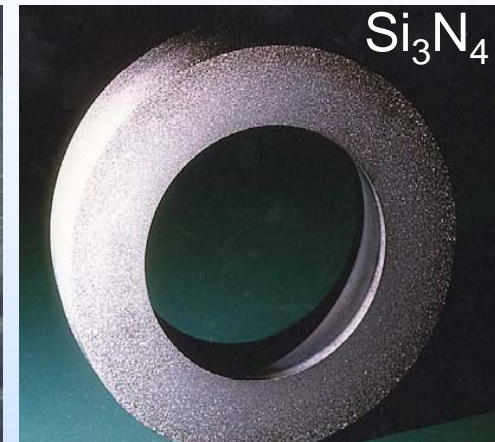
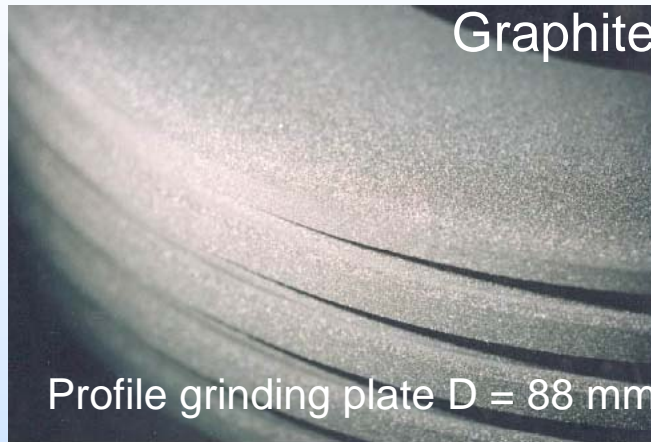
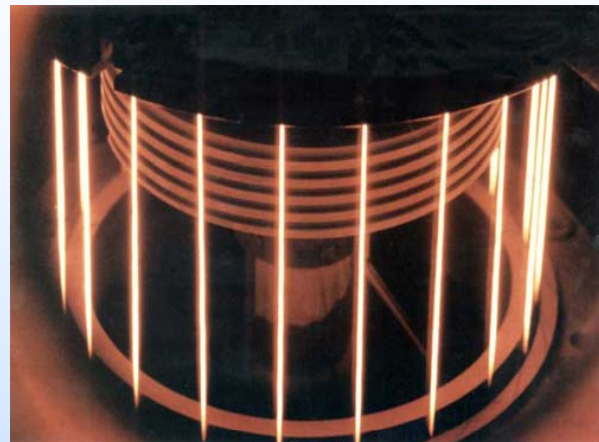


Edge of a cutting plate
with (100)-diamond film



Micro-drills $D = 0,15 \text{ mm}$

Coating of abrasive grinding tools



Small grinding pen, D = 50 μm

Main problems for the applications

- **High cost**
- **High defect density**
- **Poor film adhesion**

Large area HFCVD diamond deposition

Planar substrates with
Filament array up to
500 mm x 1000 mm





Die Diamantschicht auf den Gleitringdichtungen wächst im Vakuumbehälter unter weiß glühenden Drähten. © Rainer Meier BFF

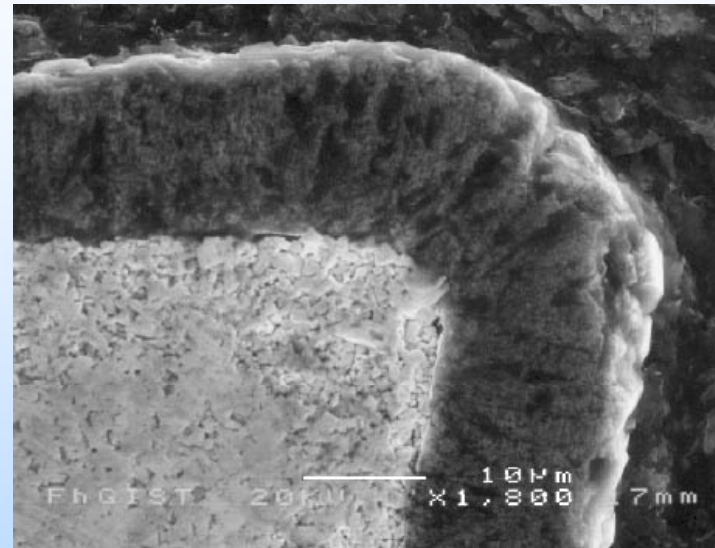
Adhesion problem prevent the application

Reason: film stress

$$\sigma_f(T) = (\alpha_s - \alpha_f)\Delta T \frac{E_f}{(1 - \nu_f)}$$

α_s, α_f : thermal expansion coefficients of substrate and film

E_f, ν_f : Young's modulus and Poisson's ratio



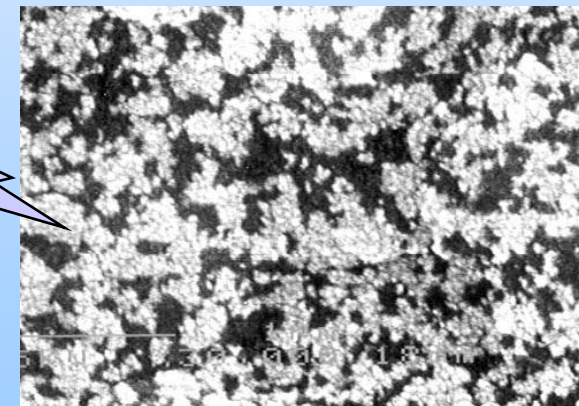
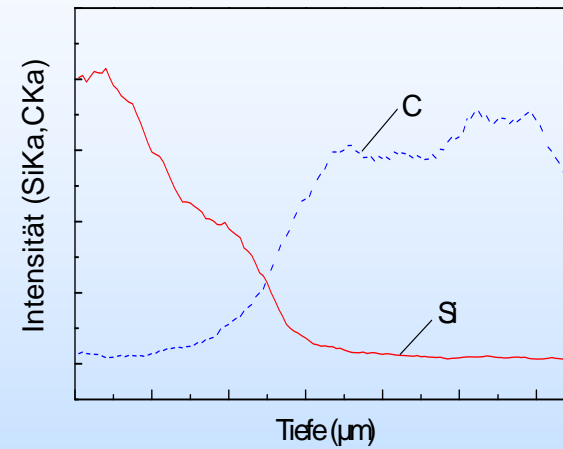
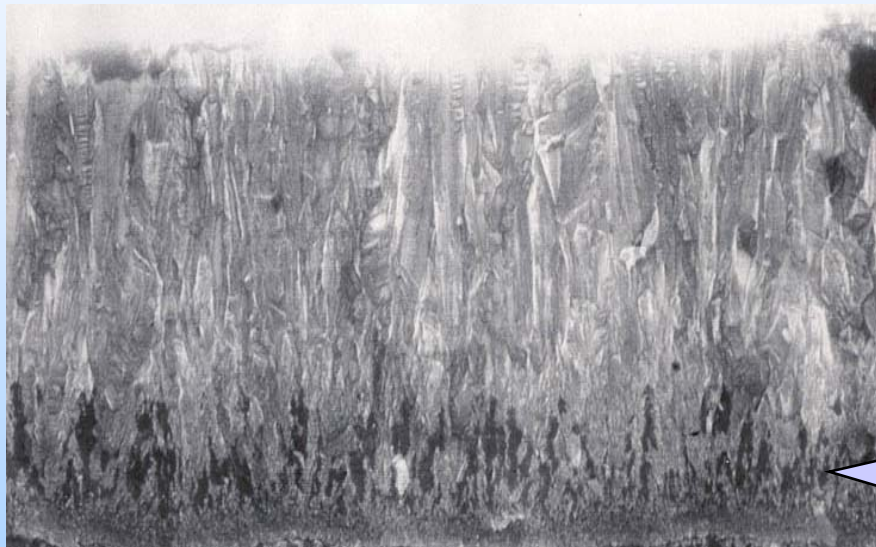
Material	Diamond	Al ₂ O ₃	Silicon	β-SiC	TiC	Steel
α (10 ⁻⁶ °C ⁻¹)	1,2	3,3	4,0	6,6	8,3	12,0
σ_f (GPa)	0,0	2,1	2,7	5,4	7,4	10,7

T_s = 800 °C

Carbide / diamond nano-composite films

Achieved syntheses

β -SiC, TiC, WC/diamond composite films



Grain size: about 10 nm

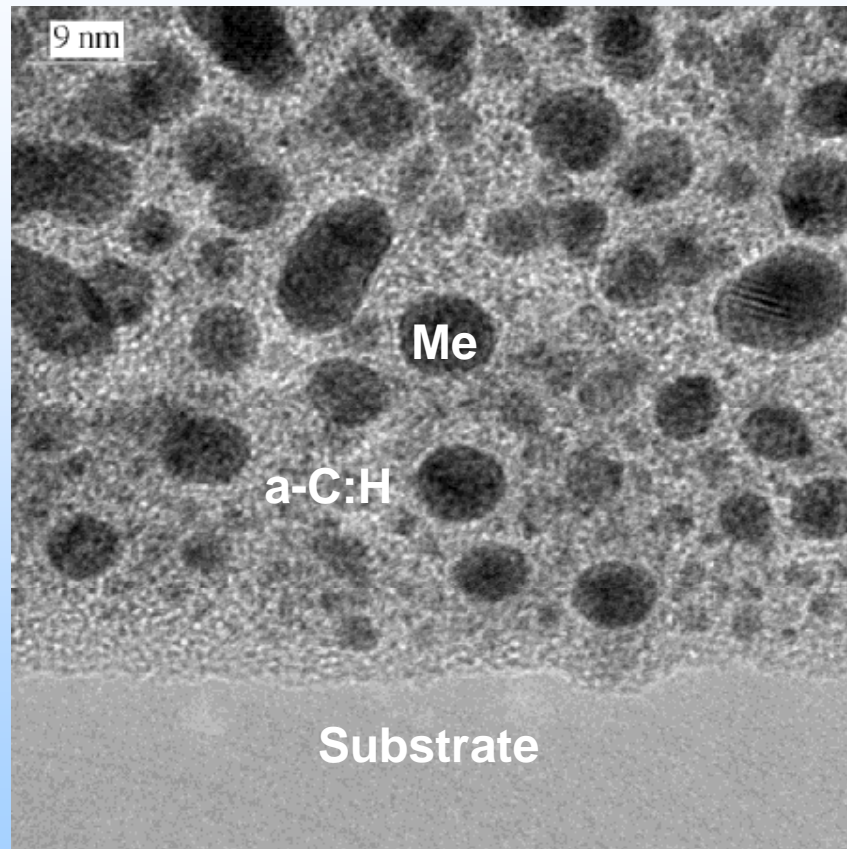
Reactive gas mixture:

$H_2/CH_4/TMS = 99,3\%/0,7\%/0,007\%$

$H_2/CH_4/Ti[OCH(CH_3)_2]_4$

$H_2/CH_4/WCl_6$

Metal / a-C:H-nanocomposite films



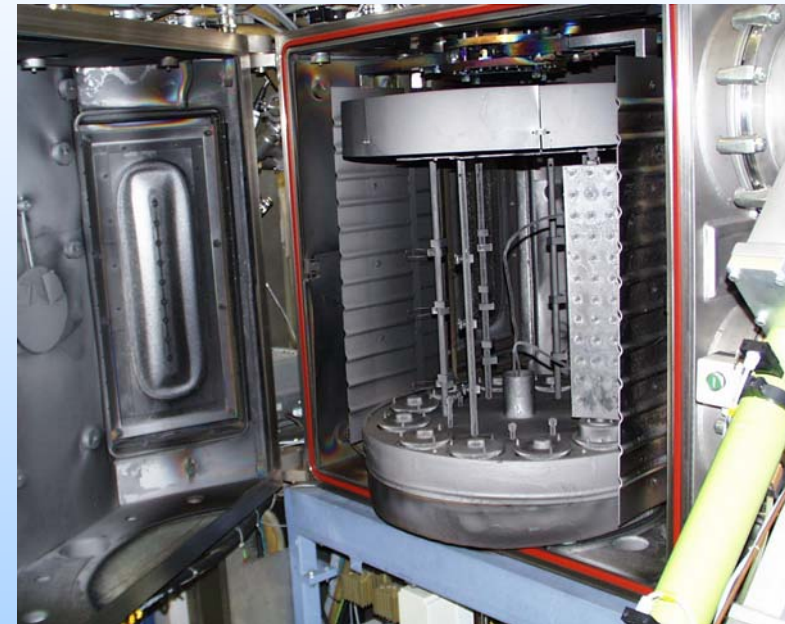
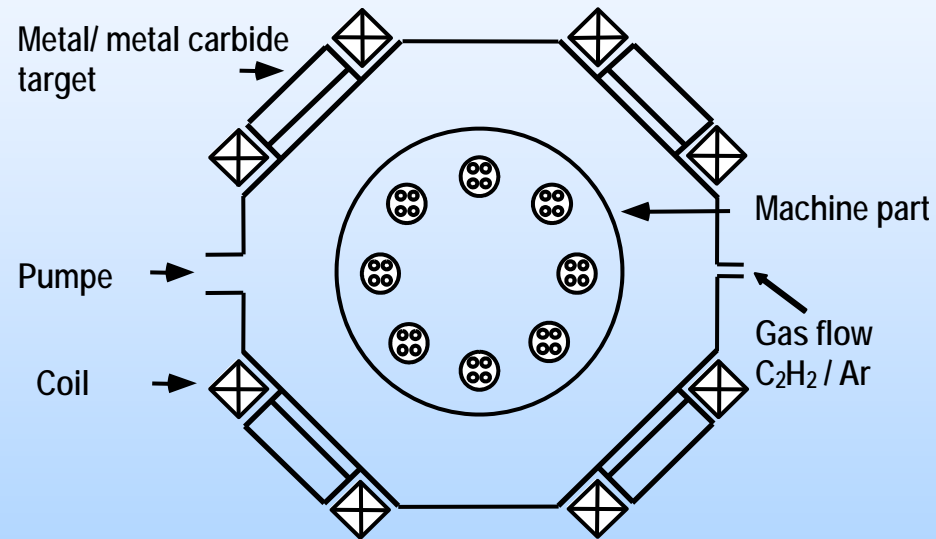
Properties:

- high adhesion strength
- High hardness (20 GPa)
- Low friction coefficient against steel ($\mu < 0,2$)
- 100 time lower wear than steel
- Biocompatible

TEM image

K. Schiffmann, Univ. Diss., Hamburg (1997), p22

HTC 1000 magnetron sputtering set up



By variation of C₂H₂ concentration a graded film preparation is possible

Application of carbon films



Antriebsselemente - Kurbelwelle für Verbrennungsmotoren:
-Reibungs- und Verschleißreduzierung
→ höhere Beschleunigung



Tablettierwerkzeug – Stempel
zum Pressen von Tabletten:
-Vermeidung des Anhaftens am
Werkzeug

In der Medizintechnik - Hüftgelenkprothese
Schutz des unbeschichteten Gegenkörpers-
kein Abrieb an der PE-Pfanne-

